Leistungsstarke IR-Lumineszenzdiode
High Power Infrared Emitter

SFH 4209



Wesentliche Merkmale

- Leistungsstarke GaAs-LED (40mW)
- Hoher Wirkungsgrad bei kleinen Strömen
- Typische Peakwellenlänge 950nm

Features

- High Power GaAs-LED (40mW)
- High Efficiency at low currents
- Typical peak wavelength 950nm

Anwendungen

- Schnelle Datenübertragung mit Übertragungsraten bis 100 Mbaud (IR Tastatur, Joystick, Multimedia)
- Analoge und digitale Hi-Fi Audio- und Videosignalübertragung
- Batteriebetriebene Geräte (geringe Stromaufnahme)
- Anwendungen mit hohen Zuverlässigkeitsansprüchen bzw. erhöhten Anforderungen
- Alarm- und Sicherungssysteme
- IR Freiraumübertragung

Applications

- High data transmission rate up to 100 Mbaud (IR keyboard, Joystick, Multimedia)
- Analog and digital Hi-Fi audio and video signal transmission
- Low power consumption (battery) equipment
- Suitable for professional and high-reliability applications
- Alarm and safety equipment
- IR free air transmission

Typ **Type**	**Bestellnummer** **Ordering Code**	**Strahlstärkegruppierung** [1] (I_F = 100mA, t_p = 20 ms) **Radiant intensity grouping** [1] I_e (mW/sr)
SFH 4209	Q62702 P5488	24 (>6.3)

[1] gemessen bei einem Raumwinkel Ω = 0.01 sr
measured at a solid angle of Ω = 0.01 sr

Grenzwerte (T_A = 25 °C)
Maximum Ratings

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**	**Einheit** **Unit**
Betriebs- und Lagertemperatur Operating and storage temperature range	T_{op}; T_{stg}	– 40 … + 100	°C
Sperrspannung Reverse voltage	V_R	3	V
Durchlaßstrom Forward current	I_F (DC)	100	mA
Stoßstrom, t_p = 10 µs, D = 0 Surge current	I_{FSM}	2.2	A
Verlustleistung Power dissipation	P_{tot}	180	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je 16 mm^2 Thermal resistance junction - ambient mounted on PC-board (FR4), padsize 16 mm^2 each	R_{thJA}	450	K/W
Wärmewiderstand Sperrschicht - Lötstelle bei Montage auf Metall-Block Thermal resistance junction - soldering point, mounted on metal block	R_{thJS}	200	K/W

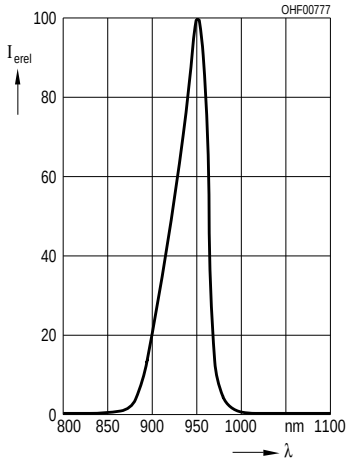
Kennwerte (T_A = 25 °C)
Characteristics

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**	**Einheit** **Unit**
Wellenlänge der Strahlung Wavelength at peak emission I_F = 100 mA, t_p = 20 ms	λ_{peak}	950	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} I_F = 100 mA, t_p = 20 ms	$\Delta\lambda$	40	nm
Abstrahlwinkel Half angle	φ	± 25	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm^2
Abmessungen der aktiven Chipfläche Dimensions of the active chip area	$L \times B$ $L \times W$	0.3 × 0.3	mm
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei I_F = 100 mA, t_p = 20 ms, R_L = 50 Ω Switching times, I_e from 10% to 90% and from 90% to10%, I_F = 100 mA, t_p = 20 ms, R_L = 50 Ω	t_r, t_f	10	ns
Durchlaßspannung, Forward voltage I_F = 100 mA, t_p = 20 ms I_F = 1 A, t_p = 100 µs	 V_F V_F	 1.5 (≤ 1.8) 3.2 (≤ 4.3)	 V V
Sperrstrom, Reverse current V_R = 3 V	I_R	0.01 (≤ 10)	µA
Gesamtstrahlungsfluß, Total radiant flux I_F = 100 mA, t_p = 20 ms	Φ_e	40	mW
Temperaturkoeffizient von I_e bzw. Φ_e, I_F = 100 mA Temperature coefficient of I_e or Φ_e, I_F = 100 mA	TC_I	– 0.44	%/K
Temperaturkoeffizient von V_F, I_F = 100 mA Temperature coefficient of V_F, I_F = 100 mA	TC_V	– 1.5	mV/K
Temperaturkoeffizient von λ, I_F = 100 mA Temperature coefficient of λ, I_F = 100 mA	TC_λ	+ 0.2	nm/K

Strahlstärke I_e in Achsrichtung
gemessen bei einem Raumwinkel Ω = 0.01 sr
Radiant Intensity I_e in Axial Direction
at a solid angle of Ω = 0.01 sr

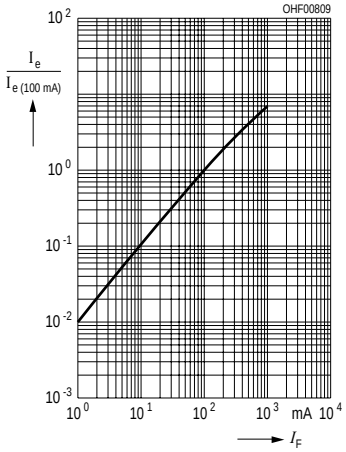
Bezeichnung **Parameter**	**Symbol**	**Werte** **Values**	**Einheit** **Unit**
Strahlstärke Radiant intensity I_F = 100 mA, t_p = 20 ms	$I_{e\ min.}$ $I_{e\ typ.}$	6,3 24	mW/sr mW/sr
Strahlstärke Radiant intensity I_F = 1 A, t_p = 100 µs	$I_{e\ typ.}$	145	mW/sr

Relative Spectral Emission
$I_{rel} = f(\lambda)$

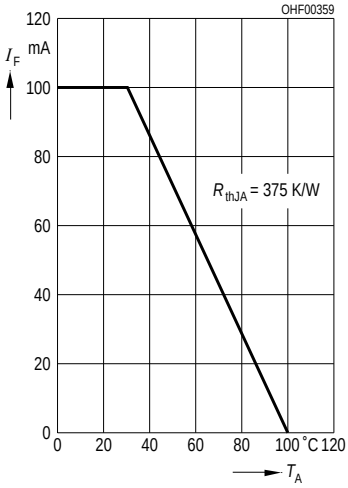


Radiant Intensity $\frac{I_e}{I_e\ 100\ mA} = f(I_F)$

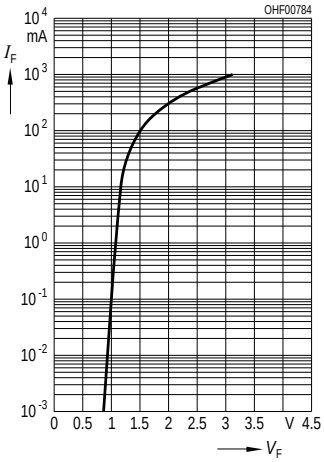
Single pulse, t_p = 20 µs



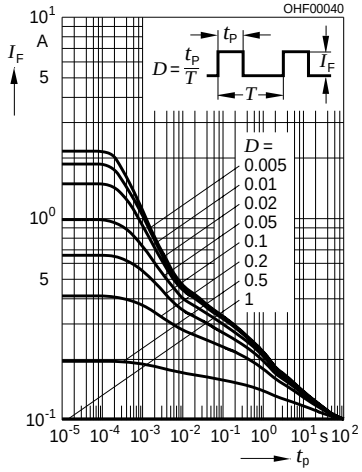
Max. Permissible Forward Current
$I_F = f(T_A)$, R_{thJA} [1)]



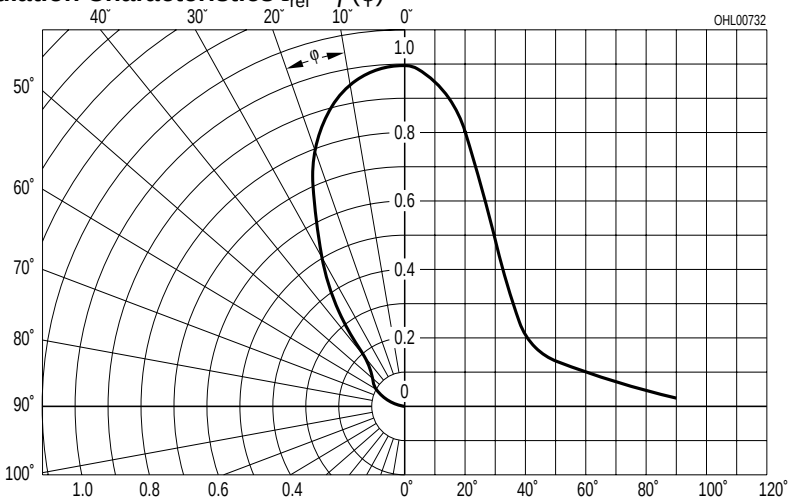
Forward Current $I_F = f(V_F)$
single pulse, t_p = 20 µs



Permissible Pulse Handling Capability $I_F = f(\tau)$, T_A = 25 °C, duty cycle D = parameter

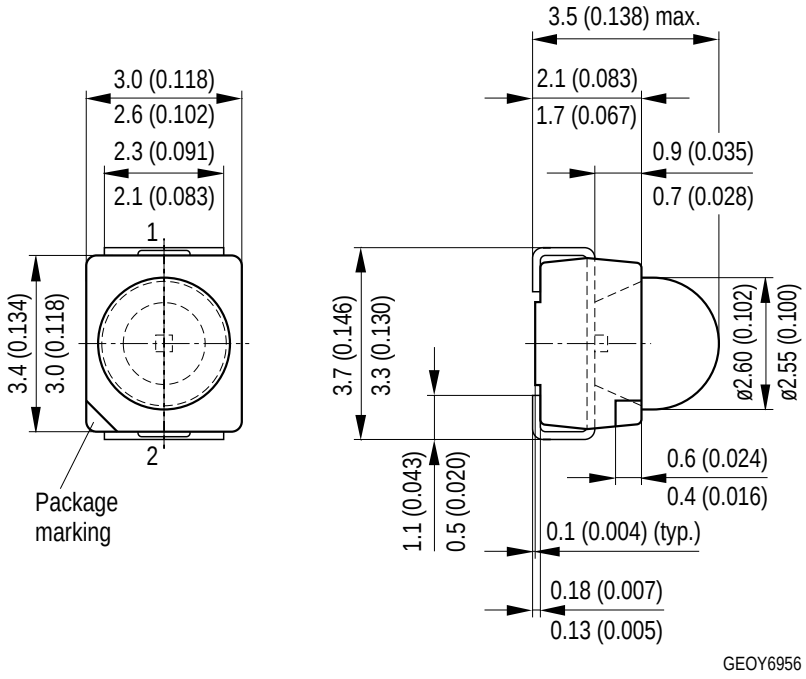


Radiation Characteristics $I_{rel} = f(\varphi)$



1) Thermal resistance junction - ambient mounted on PC-board (FR4), pad size 16 mm² (each).

Maßzeichnung
Package Outlines



Maße in mm, wenn nicht anders angegeben / Dimensions in mm, unless otherwise specified.

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